

# Si8540

## HIGH-SIDE CURRENT SENSE AMPLIFIER

#### Features

- Complete, unidirectional high-side current sense capability
- 0.2% full-scale accuracy
- +5 to +36 V supply operation
- 85 dB power supply rejection
- 90 µA max supply current
- 9 µA shutdown current
- Operating Temperature Range: -40 to +85 °C

Current control applications

- 5-pin SOT-23 package
- RoHS-compliant

Backup systems

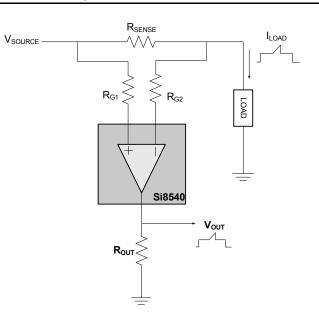
#### Applications

- Battery chargers
- Smart battery packs
- DC motor control

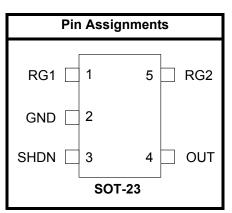
#### Description

The Si8540 is a unidirectional, 36 V (max), high-side current sense amplifier for use in applications requiring current monitoring and/or control. This device draws bias current from the high-side line to which it is attached, eliminating the need for an external supply. It measures current from 0.1 to 10 A by sensing the voltage across an external sense resistor (or PCB trace) from dc to 20 kHz and can achieve measurement accuracies of 0.2% (typical) at full load. The device output is a current signal proportional to measured current and is easily converted to a scaled voltage using a single external resistor. The Si8540 is available in compact SOT-23 package.

#### **Functional Block Diagram**







#### Patents pending



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### 1. Electrical Specifications

### Table 1. Absolute Maximum Ratings

Parameter	Value	Unit
Voltage at RG1, RG2, SHDN to GND	-0.3 to +40	V
Differential Input Voltage, RG1 to RG2	±0.3	V
Voltage at OUT	-0.3 to +8	V
Current into SHDN, GND, OUT, RG1, RG2	±50	mA
Continuous Power Dissipation (T <sub>A</sub> = +70 °C) 5-pin SOT23 derate 7.1 mW/°C above +70 °C*	571	mW
Operating Temperature Range	-40 to +85	°C
Junction Temperature, T <sub>JMAX</sub>	Up to +150	°C
*Note: The device is mounted on a standard PCB with a 100 mm <sup>2</sup> cop Permanent device damage may occur if the absolute maximum absolute maximum ratings may affect reliability. It is recommen Table 2, "DC and AC Characteristics".	n ratings are exceeded, and pro	longed use at the



#### Table 2. DC and AC Characteristics

(Unless otherwise specified:  $V_{RG1}$  = +5 to +36 V, RG1 = RG2 = 200,  $V_{SENSE}$  = 0 V,  $T_A$  = -40 to +85 °C)

Parameter	Symbol	Test Condition	Min	Тур	Max	Unit
Operating Voltage	V <sub>RG1</sub>		5		36	V
Operating Frequency	F		0	20	_	kHz
Total Input Current	I <sub>RG1</sub> +I <sub>RG2</sub>	I <sub>LOAD</sub> = 0 A		46	90	μA
Input Currents	I <sub>RG1</sub> , I <sub>RG2</sub>	I <sub>LOAD</sub> = 0 A		23	45	μA
Input Current Matching	I <sub>OS</sub>	I <sub>RG1</sub> – I <sub>RG2</sub>		±0.4	±1.5	μA
Sense Voltage <sup>1</sup>	V <sub>SENSE</sub>			100	_	mV
OUT Current Accuracy	I <sub>RG</sub> /I <sub>OUT</sub>	V <sub>SENSE</sub> = 100 mV		±0.2	±1.5	%
No-Load OUT Error		V <sub>RG1</sub> = 10 V, V <sub>SENSE</sub> = 0 V		0.5	15	μA
Low-Level OUT Error		V <sub>RG1</sub> = 10 V, V <sub>SENSE</sub> = 3 mV		±0.5	<u>+</u> 10	μA
Power-Supply Rejection	PSR	V <sub>SENSE</sub> = 100 mV	_	-85	_	dB
Shutdown Supply Current	I <sub>RG1</sub> +I <sub>RG2</sub>	V <sub>SHDN</sub> = 2.4 V	_	3.5	9	μA
SHDN Input Low Voltage	V <sub>IL</sub>		_	_	0.3	V
SHDN Input Low Current	۱ <sub>IL</sub>	V <sub>SHDN</sub> = 0 V	_		1.0	μA
SHDN Input High Voltage	V <sub>IH</sub>		2.4		_	V
SHDN Input High Current	I <sub>IH</sub>	V <sub>SHDN</sub> = 2.4 V			1.0	μA
OUT Output Voltage Range	V <sub>OUT</sub>	V <sub>OUT</sub> clamped at 8 V	0	—	V <sub>RG1</sub> – 3.5 (<8)	V
OUT Output Resistance (Internal)		I <sub>OUT</sub> = 1.5 mA	1	3		MΩ
OUT Rise, Fall Time		V <sub>SENSE</sub> = 5 mV to 150 mV, R <sub>OUT</sub> = 2 = kΩ, C <sub>OUT</sub> = 50 pF, 10% to 90% (Note 2)	_	0.4 0.5	_	µs µs
OUT Settling Time to 1% of Final Value		V <sub>SENSE</sub> = 5 to 150 mV, R <sub>OUT</sub> = 2 kΩ, C <sub>OUT</sub> = 50 pF (Note 2)	_	1 2	_	μs µs
Maximum Output Current	I <sub>OUT</sub>	For I <sub>OUT</sub> > 1.5 mA the internal current limitation starts to limit the output current	1.5		10	mA

**2.** C<sub>OUT</sub> is the load capacitance seen by the OUT pin.



### 2. Typical Application Schematic

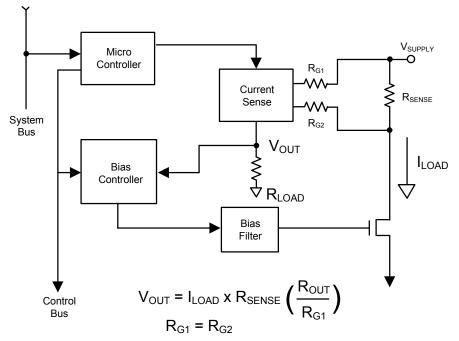


Figure 1. Connecting the Si8540 in a Power Control Application



### 3. Functional Description

The Si8540 is designed to operate over an input common-mode range of 5 to 36 V. Figure 2 shows an example Si8540 application with external sense resistor,  $R_{SENSE}$ , external current gain-setting resistors,  $R_{G1}$  and  $R_{G2}$ , and output scaling resistor,  $R_{OUT}$ . The supply current flowing into the Si8540 inverting and non-inverting inputs ( $R_{G1}$ ,  $R_{G2}$ ) is negligible compared to  $I_{LOAD}$  and, as a result, has no appreciable effect on measurement accuracy. The internal current sense amplifier measures the differential input voltage,  $V_{SENSE}$ , and generates an output current proportional to  $I_{LOAD}$ . Resistor  $R_{OUT}$  converts this current to a voltage, and its value determines the output signal gain. The Si8540 is placed in a low-power shutdown mode when SHDN is at  $V_{IH}$ .

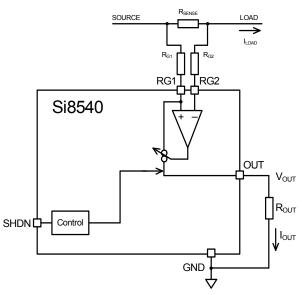


Figure 2. Si8540 Application Circuit

### 3.1. Application Information

The Si8540 can sense a wide range of currents with different sense resistor values. Table 3 lists typical operational values.

Full-scale Load Current	Current- Sense Resistor	Gain-Setting Resistors, RG1 = RG2 (Ω)	Output Resistor, R <sub>OUT</sub>	Full-Scale Output Voltage,	Scale Factor V <sub>OUT</sub> /I <sub>SENSE</sub>	and	l Error a 100% o .oad (%	f Full
I <sub>SENSE</sub> (A)	R <sub>SENSE</sub> (mΩ)		(kΩ)	V <sub>OUT</sub> (V)	(V/A)	1%	10%	100%
0.1	1000	200	5	2.5	25	10	1	0.2
1	100	200	5	2.5	2.5	10	1	0.2
5	20	100	2	2	0.4	5	1	0.2
10	5	50	2	2	0.2	5	1	0.4

Table 3. Recommended Current Sense Resistor for a Given Full-Scale Load Current



#### 3.1.1. Selecting R<sub>SENSE</sub>

Selecting  $R_{SENSE}$  involves making the best trade-off between power efficiency and accuracy. Low  $R_{SENSE}$  values dissipate less power while higher values maximize accuracy. In general, it is best to choose a relatively high value for  $R_{SENSE}$  in applications where the measured current is small. For higher current applications, the sense resistor should be able to dissipate the heat from its power loss; otherwise, its value may drift or it may fail open, possibly causing a large differential voltage across RG1 and RG2 that may damage the device. In most applications,  $R_{SENSE}$  should have low inductance to reduce the impact of any high-frequency components in the current being measured (low inductance metal film resistors are recommended). Also, note that the Si8540 requires at least 3.5 V of voltage headroom between the voltage at pin RG1 and pin OUT. This voltage headroom decreases as  $R_{SENSE}$  increases. A good guideline for determining the maximum value for  $R_{SENSE}$  is shown in the following equation:

 $R_{SENSEmax} = (V_{SOURCE} - V_{OUTmax} - 3.5 V)/I_{LOAD}$ Where:

V<sub>SOURCE</sub> is the high-side voltage

V<sub>OUTmax</sub> is the full-scale output voltage at the OUT pin

 $I_{LOAD}$  is the current passing through  $R_{SENSE}$  measured by the Si8540

#### 3.1.2. Selecting RG1 and RG2

The values of resistors  $R_{G1}$  and  $R_{G2}$  determine the sense amp current-gain. These two resistors must have the same value, and resulting current gain is equal to  $R_{SENSE} / R_G$  (where  $R_G = R_{G1} = R_{G2}$ ).

The minimum value of  $R_G$  is determined by the maximum current at the OUT pin (1.5 mA) and by the resistance between the internal current sense amp input and the sense resistor (approximately 0.2  $\Omega$ ). As the value of  $R_G$  is reduced, the input resistance becomes a larger portion of the total gain-setting resistance. This gain error can be compensated by trimming  $R_G$  or  $R_{OUT}$ . A good guideline for determining the maximum value for  $R_G$  is shown in the following equation:

R<sub>Gmax</sub> = (V<sub>SENSEmax</sub> / 1.5 mA) Where:

 $R_{Gmax}$  is the largest value for RG1 and RG2

 $V_{\mbox{SENSEmax}}$  is the value of  $V_{\mbox{SENSE}}$  at maximum  $I_{\mbox{LOAD}}$ 

Note that for a given value of V<sub>SENSE</sub>, a decrease of the R<sub>G</sub> resistor values causes a corresponding increase in current at the OUT pin. This causes additional power to be dissipated in R<sub>OUT</sub> rather than in the load, which can reduce efficiency. Note also that mismatches in the currents passing R<sub>G1</sub> and R<sub>G2</sub> (IOS) together with R<sub>G</sub> affect the full scale error.

This error can be reduced by lowering the values of  $R_{G1}$ ,  $R_{G2}$  and/or lowering their tolerances. This error can also be reduced by increasing the value of  $R_{SENSE}$ .

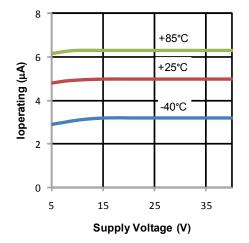
#### 3.1.3. Choosing R<sub>OUT</sub>

 $R_{OUT}$  must be chosen to generate the required full-scale output voltage at the full scale  $I_{OUT}$ , which, in turn, is determined by  $R_{G1}$ ,  $R_{G2}$ , and  $R_{SENSE}$ . The upper limit of  $R_{OUT}$  is determined by the input impedance of the device that it drives. This input impedance should be much larger than  $R_{OUT}$ ; otherwise, measurement accuracy will be degraded. A good guideline for choosing the value of  $R_{OUT}$  is shown in the following equation:

(V<sub>OUTfullscale</sub> x R<sub>G</sub>) / (I<sub>LOAD</sub> x R<sub>SENSE</sub>)

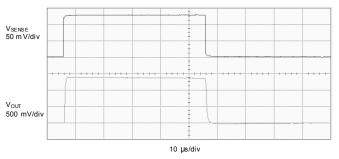


### 4. Typical Performance Data

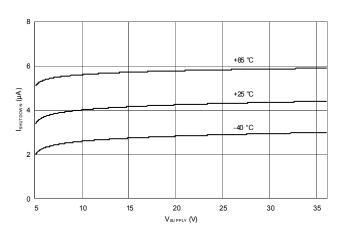


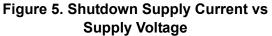
### Figure 3. Supply Current vs. Supply Voltage

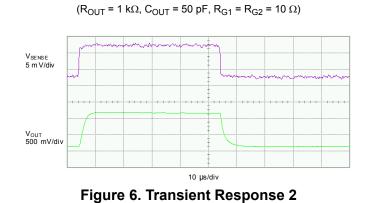
 $(\mathsf{R}_{\mathsf{OUT}}\texttt{=}2~\mathsf{k}\Omega,~\mathsf{C}_{\mathsf{OUT}}\texttt{=}50~\mathsf{pF},~\mathsf{R}_{\mathsf{G1}}\texttt{=}\mathsf{R}_{\mathsf{G2}}\texttt{=}200~\Omega)$ 



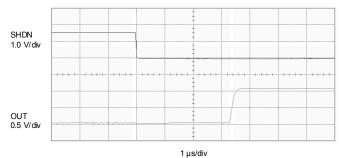




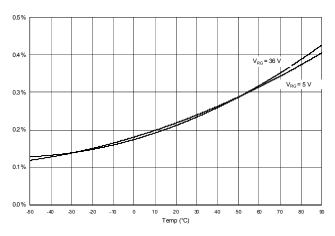




 $(\mathsf{R}_{OUT}\texttt{=}2\text{ k}\Omega,\,\mathsf{C}_{OUT}\texttt{=}50\text{ pF},\,\mathsf{R}_{G1}\texttt{=}\mathsf{R}_{G2}\texttt{=}200\ \Omega,\,\mathsf{V}_{SENSE}\texttt{=}100\text{ mV})$ 











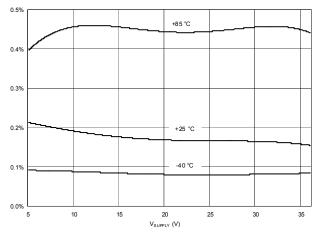


Figure 9. Output Error vs. Supply Voltage

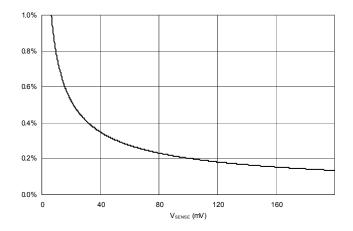
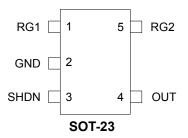


Figure 10. Output Error vs. Sense Voltage



### 5. Pin Descriptions



### Figure 11. Pin Configuration

### Table 4. Pin Descriptions

Pin Number	Name	Description				
	SOT23					
1	RG1	Power-side input.				
2	GND	Ground.				
3	SHDN	Shutdown input. Ground for normal operation. High voltage for shutdown.				
4	OUT	Current output.				
5	RG2	Load-side input.				



### 6. Ordering Guide

Ordering Part # <sup>1</sup>	Temperature Range	Package
Si8540-B-FW	–40 to +85 °C	SOT-23 <sup>2</sup>
	·	

Notes:

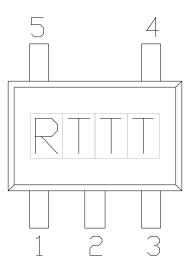
1. Tape and reel options are specified by adding an "R" suffix to the ordering part number. Example: "Si8450-B-FWR" indicates the SOT-23 package option in a tape and reel carrier.

2. Moisture sensitivity level (MSL) is (MSL2A) for SOT-23 package with peak reflow temperature of (260 °C) according to JEDEC industry-standard classifications.



### 6.1. Device Marking

### 6.1.1. SOT-23 Package Top Mark



### 6.1.2. Top Marking Explanation

Line 1 Marking:	Manufacturing trace code	R = Device revision (B)
		TTT = Assembly trace code



### 7. Package Outline: SOT-23

Figure 12 illustrates the package details for the SOT-23. Table 5 lists the values for the dimensions shown in the illustration.

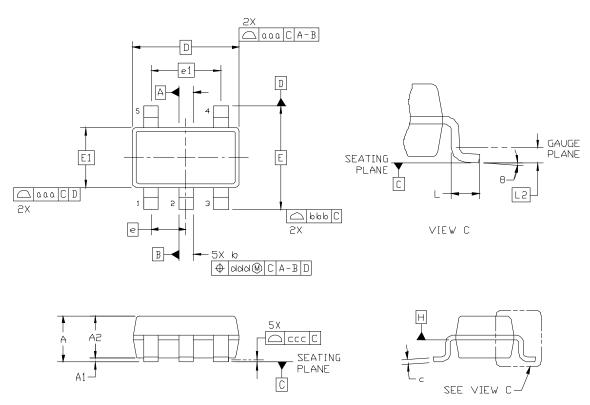


Figure 12. SOT-23 Package

Dimension	Min	Max	Dimension	Min	Мах
А	_	1.45	E1	1.90	BSC
A1	0.00	0.15	L	0.30	0.60
A2	0.90	1.30	L2	0.25	BSC
b	0.30	0.50	θ	0°	8°
С	0.08 0.20		aaa	0.	15
D	2.90 BSC		bbb	0.	20
E	2.80 BSC		CCC	0.	10
E1	1.60 BSC		ddd	0.	20
е	0.95 BSC				

Notes:

1. All dimensions shown are in millimeters (mm) unless otherwise noted.

**2.** Dimensioning and Tolerancing per ANSI Y14.5M-1994.

3. This drawing conforms to the JEDEC Solid State Outline MO-178, Variation AA.

4. Recommended card reflow profile is per the JEDEC/IPC J-STD-020D specification for Small Body Components.



### 8. Land Pattern: SOT-23

Figure 13 illustrates the recommended land pattern details for the SOT-23 device. Table 6 lists the values for the dimensions shown in the illustration.

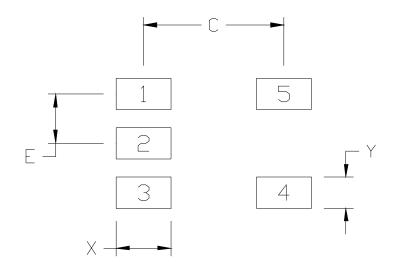


Figure 13. SOT-23 Land Pattern

#### Table 6. SOT-23 Land Pattern Dimensions

Dimension	(mm)
С	2.70
E	0.95
X	1.05
Y	0.60

Notes:

General

- **1.** All dimensions shown are in millimeters (mm) unless otherwise noted.
- 2. Dimensioning and Tolerancing is per the ANSI Y14.5M-1994 specification.
- 3. This Land Pattern Design is based on the IPC-7351 guidelines.
- **4.** All dimensions shown are at Maximum Material Condition (MMC). Least Material Condition (LMC) is calculated based on a Fabrication Allowance of 0.05 mm.

#### Card Assembly

- **5.** A No-Clean, Type-3 solder paste is recommended.
- **6.** The recommended card reflow profile is per the JEDEC/IPC J-STD-020D specification for Small Body Components.



### **DOCUMENT CHANGE LIST**

### Revision 2.5 (July 2007 Integration Associates) to Revision 1.0 (March 2010 Silicon Laboratories)

- Reformatted document from IA2410 and renamed Si8540.
- Updated " Functional Block Diagram" on page 1.
- Updated " Description" on page 1.
- Updated Table 2 on page 5.
  - OUT current accuracy changed from ±1 to ±1.5%. (max)
  - No-Load OUT Error changed from 5 to 15 µA (max)
  - Low-Level OUT Error changed from ±5 to ±10 µA (max)
     Temperature output error test conditions note updated
  - Temperature output error test conditions note updated to include temperature range of –40 to TBD° C.
- Updated "3. Functional Description" on page 7.
- Updated "3.1.1. Selecting R<sub>SENSE</sub>" on page 8.
- Updated "3.1.2. Selecting RG1 and RG2" on page 8.
- Updated "3.1.3. Choosing R<sub>OUT</sub>" on page 8.
- Removed temperature sensing function throughout.
- Added recommended PCB Land Pattern sections.
- Reformatted document from "IA2410 Rev 2.5" (Integration Associates) and renamed and rereleased as "Si8540 Rev 1.0" (which obsoletes the previous preliminary internal revision 2.6).

### **Revision 1.0 to Revision 1.1**

- MSL for the SOT-23 package improved to MSL2A (see "6. Ordering Guide" on page 12).
- Added "6.1. Device Marking" on page 13.

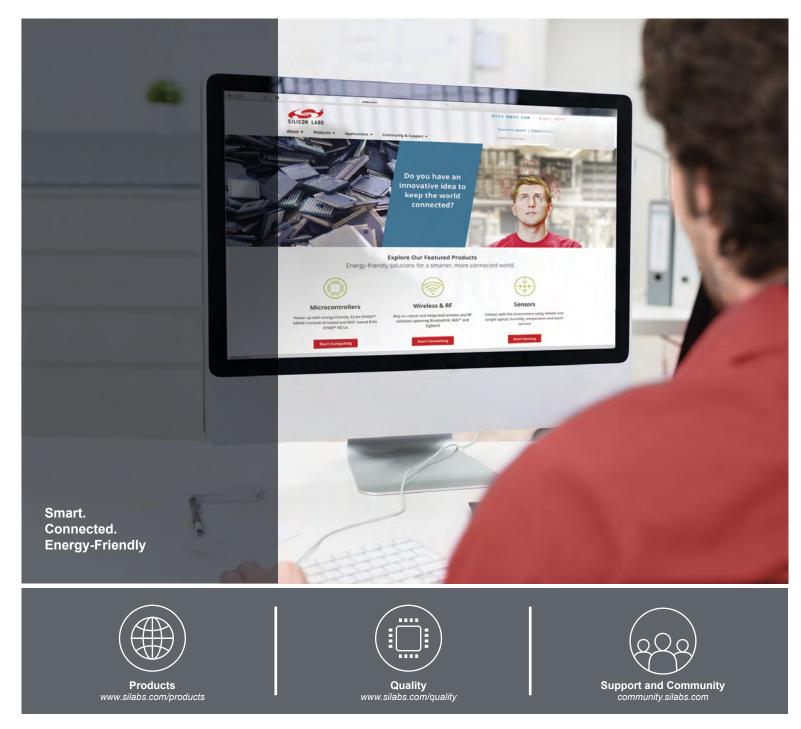
### **Revision 1.1 to Revision 1.2**

Removed SOIC-8 package throughout document.



### NOTES:





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